

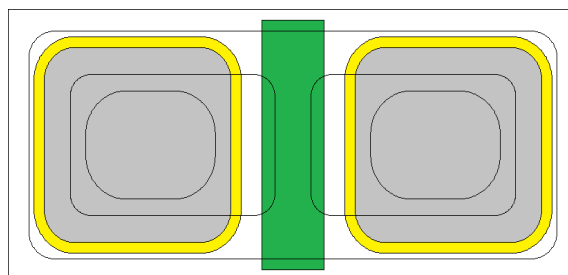
OSZ-2056026PF-8V(AuSn)

SILICON ZENER DIODE

BIDIRECTIONAL ZENER DIODE (FLIP TYPE)

APPLICATION : Surge ESD Protector

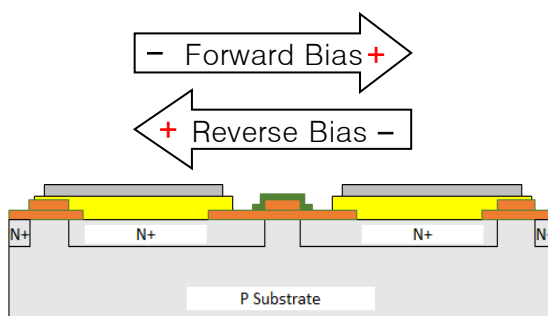
- DIE SIZE $0.54(\pm 0.025)\text{mm} \times 0.24(\pm 0.025)\text{mm}$
- DIE THICKNESS $150 \pm 20\mu\text{m}$ or $210 \pm 20\mu\text{m}$
- METALLIZATION
 - TOP AuSn
 - BOTTOM None
- SOLDER THICKNESS $4\mu\text{m}$
- BONDING PAD SIZE
 - CATHODE(TOP) $0.18\text{mm} \times 0.18\text{mm}$
 - ANODE(TOP) $0.18\text{mm} \times 0.18\text{mm}$



● ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V_Z	$I_F=5\text{mA}$	7.0	8.0	9.5	V
Zener Voltage	V_Z	$I_Z=5\text{mA}$	7.0	8.0	9.5	V
Reverse Current	I_R	$V_R=4\text{V}$			0.1	μA
Forward Current	I_F	$V_F=4\text{V}$			0.1	μA

● THE DIRECTION OF BIAS IS USED TO ELECTRICAL CHARACTERISTICS TEST (SYMMETRY)



● ABSOLUT MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	100	mW
Junction Temperature	T_J	150	$^\circ\text{C}$

● ORDER FORM

	THICKNESS(μm) ($\pm 20\mu\text{m}$)
OSZ-2056026PF-8V15(AuSn)	150
OSZ-2056026PF-8V21(AuSn)	210

BIDIRECTIONAL ZENER DIODE (FLIP TYPE)

PART NAME : ZENER DIODE

PART NUMBER : OSZ-2056026PF-8V(AuSn)

